

86397

PATENT

#4/a
BN
7/9/02IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Patent Application)
)
 Applicants: Satoshi Komiya, Shiro Yoshino)
 Masayoshi Danbata and)
 Kouichirou Hayashida)
)
 Serial No.: Not Yet Assigned)
)
 Filed: Herewith)
)
 For: **Silicon Wafer and Method For Manufacturing**)
Thereof, and Method)
For Evaluation of Silicon Wafer)

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
 Washington, D.C. 20231

Sir:

This is a Preliminary Amendment for entry in the above-identified application.

In the Claims:

Please amend claims 3 and 5 as follows:

3. (amended) A silicon wafer for non-oxidative heat treatment for use in semiconductor device manufacture according to claim 1, wherein the silicon wafer is a silicon wafer for hydrogen heat treatment or a silicon wafer for argon annealing.

5. (amended) A silicon wafer for manufacturing a semiconductor device manufactured by hydrogen heat treatment or argon annealing of the silicon wafer for non-oxidative heat treatment according to claim 1.

Respectfully submitted,

WELSH & KATZ, LTD.

Date: February 12, 2002

Welsh & Katz, Ltd.
 120 South Riverside Plaza, 22nd Floor
 Chicago, Illinois 60606
 312-655-1500

By *Gerald T. Shekleton*
 Gerald T. Shekleton
 Registration No. 27,466